









B2D06065Q

650V ▲ 6A ▲ SIC SCHOTTKY DIODE

SILICON CARBIDE SIC SCHOTTKY DIODE ▲ SMD type

Excellent surge capability

Easy paralleling due to positive V_F temperature coefficient

Flat DFN 8x8 package ▲ Epoxy meets UL94-V0 ▲ MSL3

Temperature independent switching

Ultra-low forward voltage and high surge current

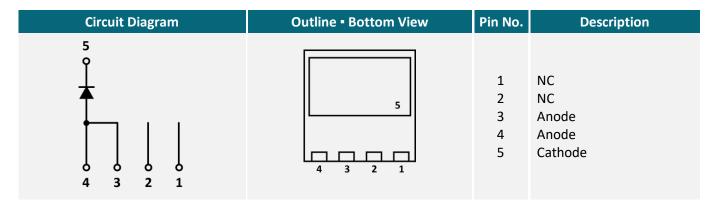
SPECIFICATION

Item (T _c = 25°C, unless otherwise noted)	Characteristics	
Operating Temperature Range	T _J	-55°C to +175°C
Storage Temperature Range	Ts	-55°C to +175°C
Repetitive Peak Reverse Voltage	V_{RRM}	650V
Continuous Forward Current at T _c = 160°C	I _F	6A
Total Capacitive Charge (T _J = 25°C)	\mathbf{Q}_{c}	17nC
Capacitance Stored Energy (V _R = 400V)	Ec	4.5μJ
Diode Forward Voltage (T _J = 175°C, I _F = 6A)	V_{F}	1.63V
Power Dissipation	P _{TOT}	98W

APPLICATIONS

EV Charging	Industrial Inverters	Motors & Drives	Power Factor Correction	Renewable Energy	SMPS	UPS
∳ / /=	0		PFC	*		

PIN DESCRIPTION



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ABSOLUT MAXIMUM RATINGS ▲ T_C = 25°C, unless otherwise noted

Item	Condition	Symbol		Unit
Repetitive Peak Reverse Voltage		V_{RRM}	650	V
Non-Repetitive Peak Reverse Voltage		V_{RSM}	650	V
Continuous Forward Current	T _C = 25°C	I _F	23	Α
Continuous Forward Current	$T_C = 160^{\circ}C$	I _F	6	Α
Non-Repetitive Forward Surge Current	T_C = 25°C, t_p = 10ms, Half Sine Wave	I _{FSM}	45	Α
I ² t Value	$T_C = 25^{\circ}C$, $t_p = 10$ ms	∫i²dt	10.12	A^2s
Power Dissipation	T _C = 25°C	P _{TOT}	98	W
Power Dissipation	$T_C = 110^{\circ}C$	P_{TOT}	42	W
Operating Junction Temperature		TJ	-55 to +175	°C
Storage Temperature Range		T_{STG}	-55 to +175	°C

ELECTRICAL CHARACTERISTICS

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Static Characteristics						
DC Blocking Voltage	T _J = 25°C	V_{DC}	650			V
Diode Forward Voltage	$I_F = 6A, T_J = 25^{\circ}C$	V_{F}		1.33	1.50	V
Diode Forward Voltage	$I_F = 6A, T_J = 175^{\circ}C$	V_{F}		1.63	2.20	V
Reverse Current	$V_R = 650V$, $T_J = 25$ °C	I_R		1	50	μΑ
Reverse Current	$V_R = 650V$, $T_J = 175$ °C	I_R		20	200	μΑ
Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Dynamic Characteristics						
	$V_R = 400V, T_J = 25^{\circ}C$					
Total Capacitive Charge	$Q_C = \int_0^{V_R} C(V) dV$	Qc		17		nC
Total Capacitance	$V_R = 1V$, $f = 1MHz$, $T_J = 25$ °C	С		271		pF
Total Capacitance	$V_R = 300V$, $f = 1MHz$, $T_J = 25$ °C	С		30.1		pF
Total Capacitance	V_R = 600V, f = 1MHz, T_J = 25°C	С		29.8		pF
Capacitance Stored Energy	$V_R = 400V$, $T_J = 25$ °C	E _C		4.5		μЈ

THERMAL RESISTANCE PERFORMANCE

Item	Symbol	Min.	Тур.	Max.	Unit
Thermal Resistance, Junction to Case	$R_{\theta,JC}$		1.520		K/W



REFERENCE DATA A TYPICAL PERFORMANCE

Fig. 1 • Typical Forward Characteristics I_F vs. V_F

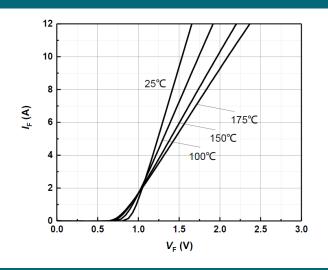


Fig. 2 • Typical Reverse Current I_R as function of Reverse Voltage V_R

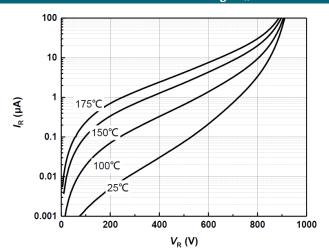


Fig. 3 • Diode Forward Current I_F as function of Case Temperature T_C (D = Duty Cycle)

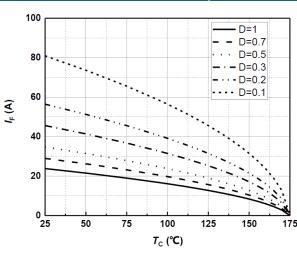


Fig. 4 • Typical Capacitance C as function of Reverse Voltage V_R , $C = f(V_R)$, $T_J = 25^{\circ}C$, f = 1MHz

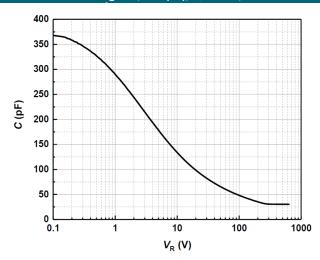


Fig. 5 • Typical Reverse Charge Q_C as function of Reverse Voltage V_R

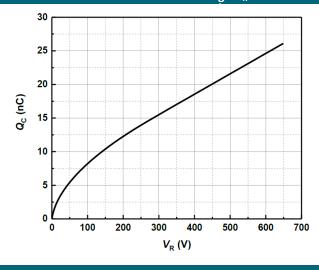
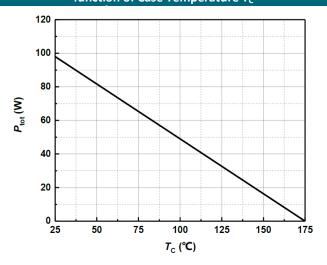


Fig. 6 • Power Dissipation P_{TOT} as function of Case Temperature T_C



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REFERENCE DATA A TYPICAL PERFORMANCE

Fig. 7 • Capacitance Stored Energy

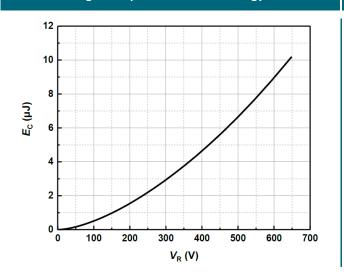
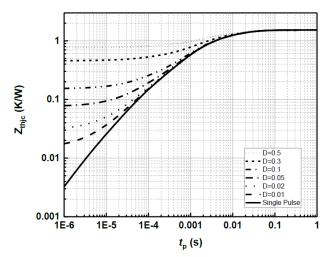
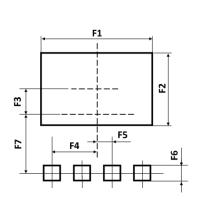


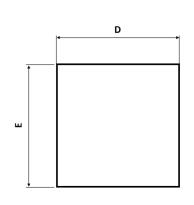
Fig. 8 • Maximum Transient Thermal Impedance, Z_{thjc} = f(t), Parameter: D = t/T

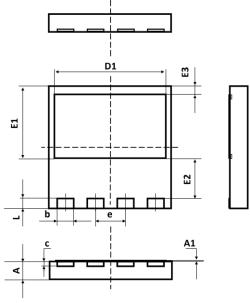




PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT







Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
Α	0.90	1.00	1.10
A1	0.00	-	0.05
b	0.90	1.00	1.10
С	0.10	0.20	0.30
D	7.90	8.00	8.10
D1	7.10	7.20	7.30

Sym	Millimeters (Min.)			
Е	7.90	8.00	8.10	
E1	4.65	4.75	4.85	
E2	2.65	2.75	2.85	
E3	0.30	0.40	0.50	
e		2.00 BSC		
L	0.40	0.50	0.60	

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	7.20	-
F2	-	4.75	-
F3	-	1.43	-
F4	-	3.00	-

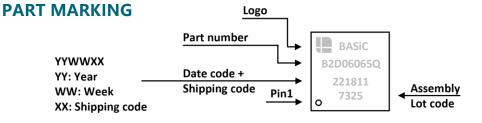
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F5	-	1.00	-
F6	-	1.00	-
F7	-	4.20	-

Notes: 1. The suggested land pattern dimensions have been provided for reference only.

2. For further information, please reference document IPC-7351A.

ORDERING INFORMATION

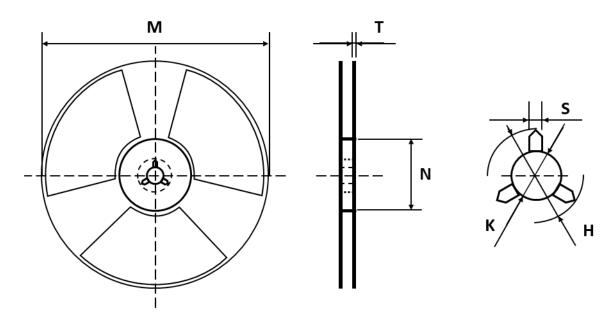
Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
B2D06065Q	DFN 8x8	Reel	3,000pcs	6,000pcs	36,000pcs



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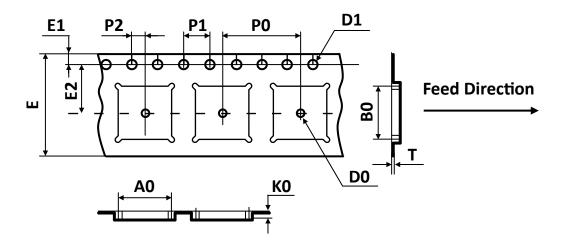


REEL DIMENSIONS ▲ All dimensions in mm



Tape Size	Reel Size	M	N	Т	Н	K	S
		Ø330.00	Ø102.00	2.00	13.00	10.50	2.00
24mm	Ø330	±0.20	±0.10	±2.0	+0.50 -0.20	±0.25	±0.25

TAPE DIMENSIONS ▲ All dimensions in mm

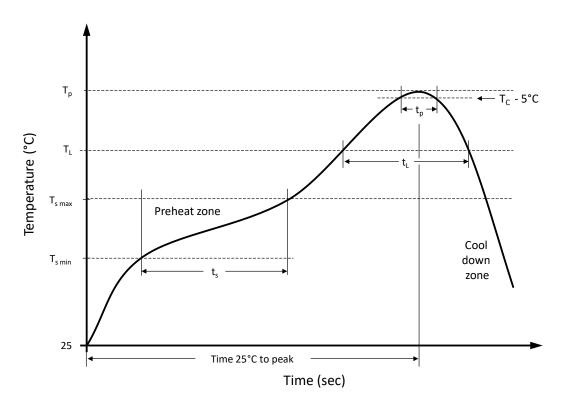


	Package	Α0	В0	КО	D0	D1	E	E1	E2	P0	P1	P2	Т
DFN 8x8	DENI OVO	8.30	8.30	1.15	1.50	1.50	24.00	1.75	7.50	12.00	4.00	2.00	0.30
	DEIN OXO	±0.10	±0.10	±0.10	±0.10	±0.10	±0.30	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05

Note: All dimensions meet EIA-481-D requirements.



RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T _{s max}	150 °C	200 °C
Preheat time t _s from T _{s min} to T _{s max}	ts	120 seconds	120 seconds
Ramp-up rate (T₁ to Tp)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	T_L	183 °C	217 °C
Time t _L maintained above T _L	t _L	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t _p	20 seconds max.	30 seconds max.
Ramp-down rate (T _L to T _p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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